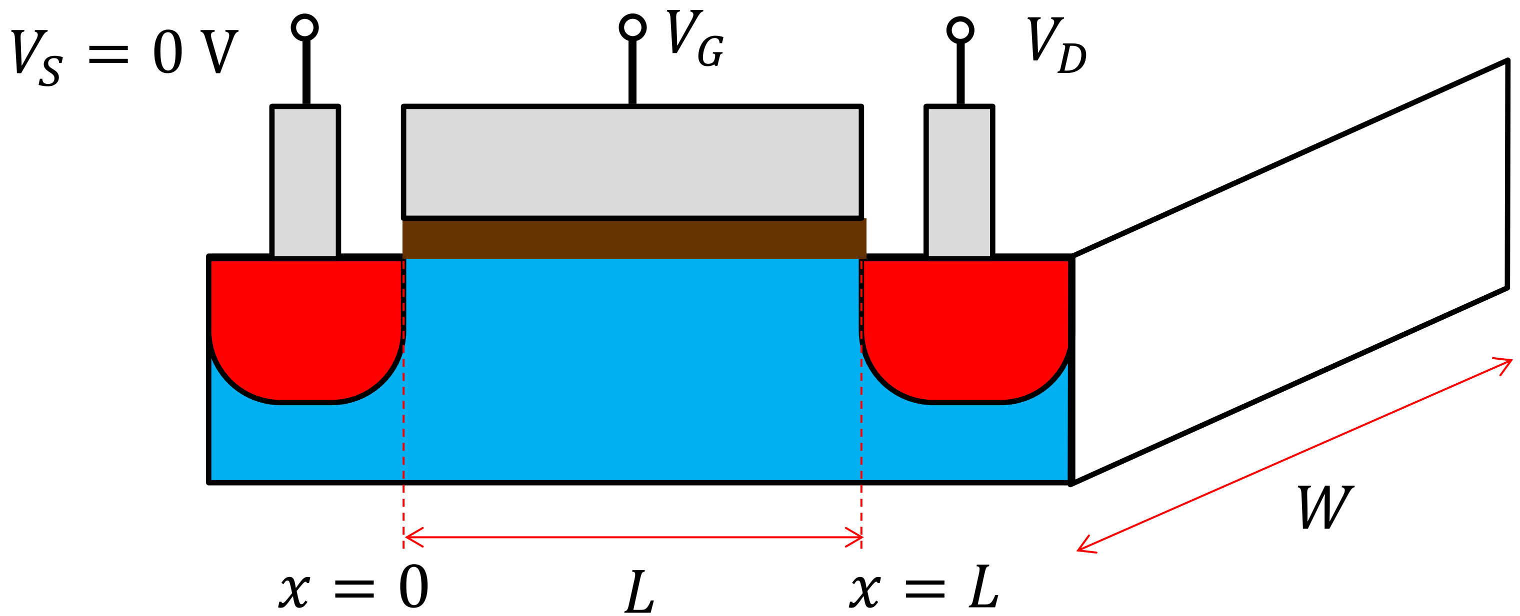
Lecture11: MOSFET IV

Sung-Min Hong (smhong@gist.ac.kr)

Semiconductor Device Simulation Lab.
School of Electrical Engineering and Coumputer Science
Gwangju Institute of Science and Technology

Device structure

- Two-dimensional cross-section
  - “Potential” can be dependent on the position, $V(x)$.



Derivation of IV (1)

- Drain current
  - Q_{elec} is the electron charge density *per unit length*.
  - It follows

$$Q_{elec} = WC_{ox}[V_G - V(x) - V_{TH}] \qquad \text{(Razavi 6.3)}$$

  - At a certain position of x, the current is given by

$$I(x) = Q_{elec}(x)\, v(x) \qquad \text{(Razavi 6.4)}$$

  - Also v is the electron velocity.

$$v = -\mu_n E = +\mu_n \frac{dV}{dx} \qquad \text{(Razavi 6.5 and 6.6)}$$

Derivation of IV (2)

- Drain current (Continued)
  - It is easy to understand that $I_D = I(x)$. The drain current is

$$I_D = WC_{ox}[V_G - V(x) - V_{TH}]\mu_n \frac{dV}{dx} \qquad \text{(Razavi 6.7)}$$

  - Simply re-arranging,

$$I_D dx = \mu_n C_{ox} W[V_G - V(x) - V_{TH}]dV$$

  - When integrated,

$$I_D = \mu_n C_{ox} \frac{W}{L}\left[(V_G - V_{TH})V_{DS} - \frac{1}{2}V_{DS}^2\right]$$

Triode mode

- Equation
  - A differential equation for $V(x)$

$$I_D = W C_{ox}[V_G - V(x) - V_{TH}]\mu_n \frac{dV}{dx}$$

  - Its solution

$$V(x) = V_G - V_{TH} - \sqrt{(V_G - V_{TH})^2 - \frac{2I_D}{\mu_n C_{ox} W} x}$$

  - Drain current

$$I_D = \mu_n C_{ox} \frac{W}{L}\left[(V_G - V_{TH})V_{DS} - \frac{1}{2}V_{DS}^2\right]$$

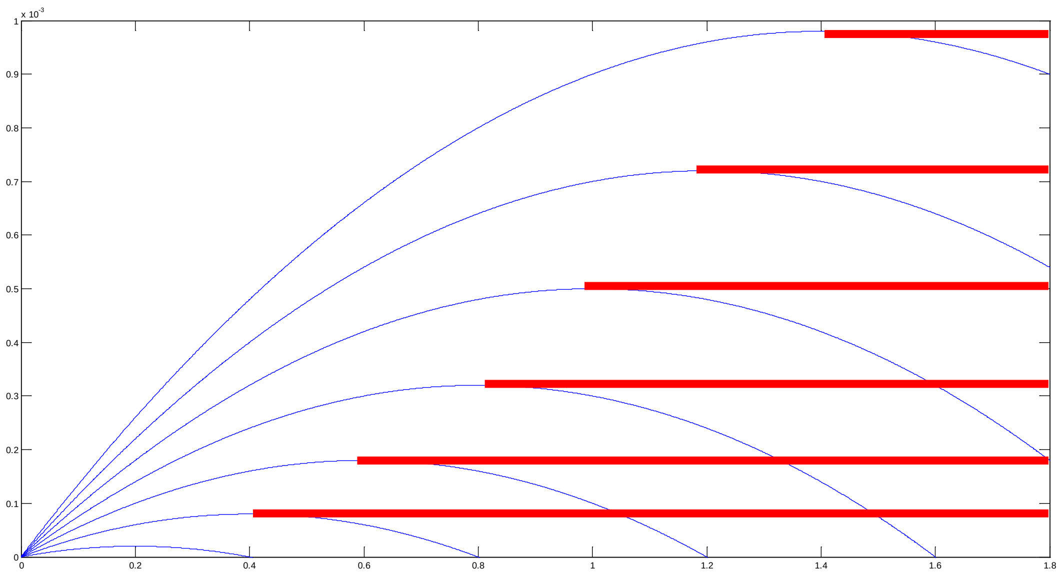
Saturation mode

- Current usually increases as the voltage increases…

$$|Q_{elec}| = WC_{ox}[V_G - V(x) - V_{TH}]$$ (Razavi 6.3)

  – What happens when $V(x) = V_G - V_{TH}$?

Current



Voltage

🡐 Instead, the current is saturated. (Red lines)

State-of-the-art MOSFET

- C. Auth et al. (Intel, IEDM 2017)
  - Slight increase of I_D in the satruation region